

## N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>d</sup>	Q <sub>g</sub> (Typ.)
20	0.028 at V <sub>GS</sub> = 4.5 V	7.9	6.7 nC
	0.032 at V <sub>GS</sub> = 2.5 V	7.4	
	0.038 at V <sub>GS</sub> = 1.8 V	6.8	

### FEATURES

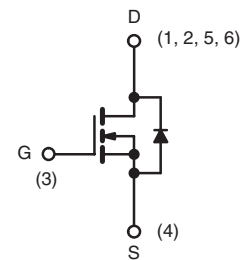
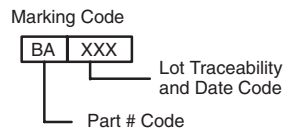
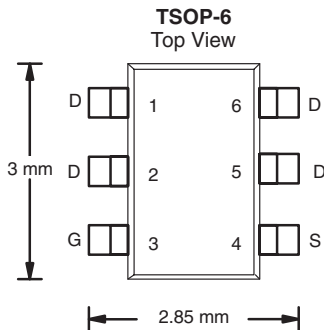
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- DC/DC Converters
- Boost Converters
- Load Switch



Ordering Information: Si3460DDV-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	± 8	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	7.9	A
	T <sub>C</sub> = 70 °C	6.3	
	T <sub>A</sub> = 25 °C	6.2 <sup>a, b</sup>	
	T <sub>A</sub> = 70 °C	5.0 <sup>a, b</sup>	
Pulsed Drain Current	I <sub>DM</sub>	20	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	2.2	
	T <sub>A</sub> = 25 °C	1.4 <sup>a, b</sup>	
Avalanche Current	I <sub>AS</sub>	8	
Single Avalanche Energy	E <sub>AS</sub>	3.2	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	2.7	W
	T <sub>C</sub> = 70 °C	1.7	
	T <sub>A</sub> = 25 °C	1.7 <sup>a, b</sup>	
	T <sub>A</sub> = 70 °C	1.1 <sup>a, b</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, c</sup>	t ≤ 5 s	R <sub>thJA</sub>	61	74	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	38	46	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 120 °C/W.
- Based on T<sub>C</sub> = 25 °C.

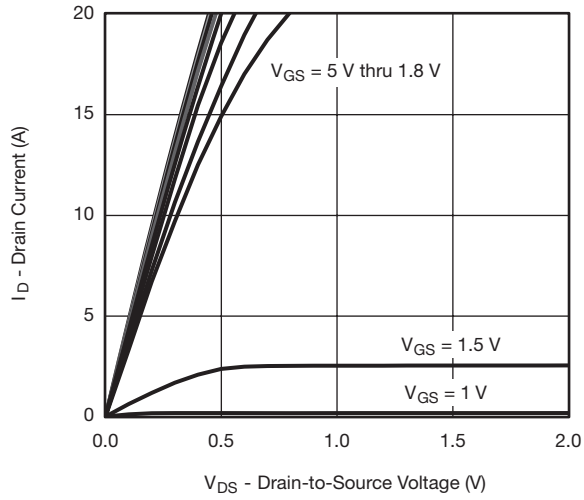
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		21		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 2.6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.4		1.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = 4.5\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 5.1\text{ A}$		0.023	0.028	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 4.7\text{ A}$		0.027	0.032	
		$V_{GS} = 1.8\text{ V}, I_D = 2.5\text{ A}$		0.031	0.038	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 5.1\text{ A}$		35		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		666		pF
Output Capacitance	$C_{oss}$			93		
Reverse Transfer Capacitance	$C_{rss}$			41		
Total Gate Charge	$Q_g$	$V_{DS} = 10\text{ V}, V_{GS} = 8\text{ V}, I_D = 5\text{ A}$		12	18	nC
		$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$		6.7	10.1	
Gate-Source Charge	$Q_{gs}$			0.95		
Gate-Drain Charge	$Q_{gd}$			0.5		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.4	2.1	4.2	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		6	12	ns
Rise Time	$t_r$			11	20	
Turn-Off Delay Time	$t_{d(off)}$			21	32	
Fall Time	$t_f$			8	16	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 8\text{ V}, R_g = 1\text{ }\Omega$		5	10	
Rise Time	$t_r$			12	18	
Turn-Off Delay Time	$t_{d(off)}$			19	29	
Fall Time	$t_f$			8	16	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			2.2	A
Pulse Diode Forward Current	$I_{SM}$				20	
Body Diode Voltage	$V_{SD}$	$I_S = 5\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		11	20	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			3	6	nC
Reverse Recovery Fall Time	$t_a$			7		ns
Reverse Recovery Rise Time	$t_b$			4		

## Notes:

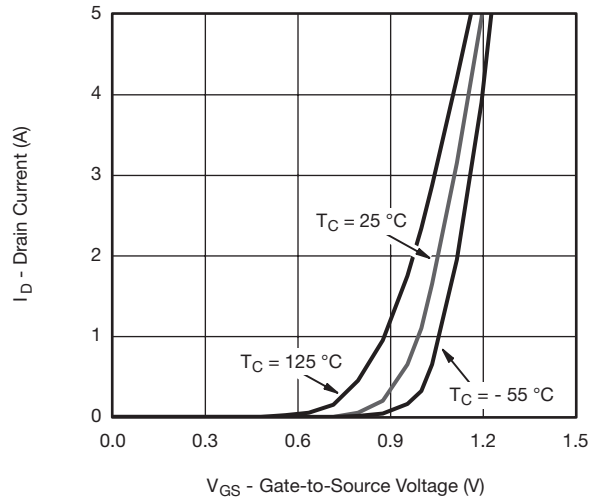
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

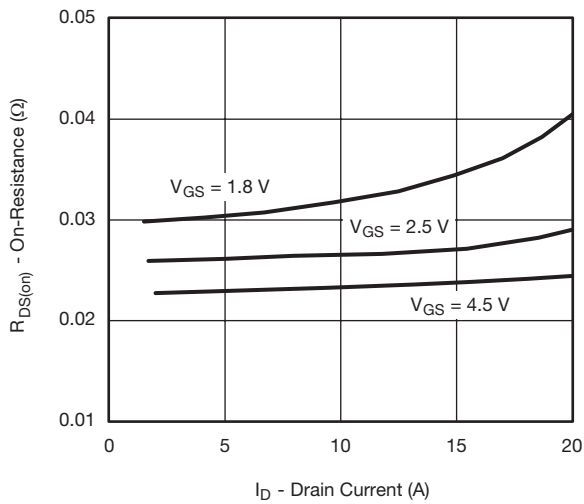
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



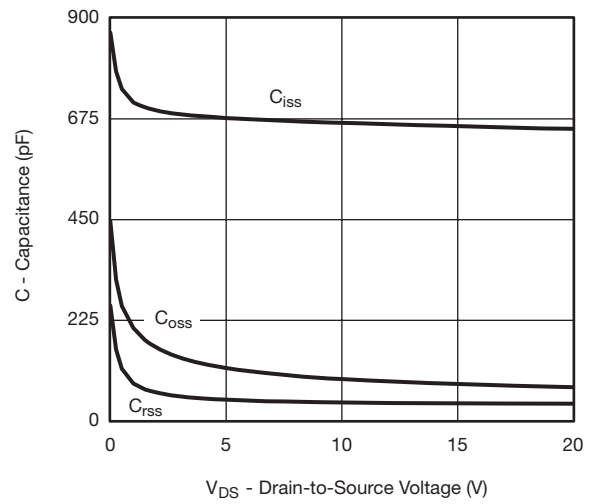
**Output Characteristics**



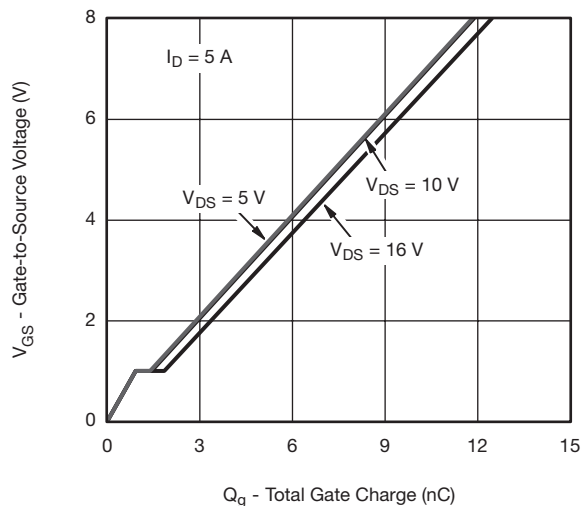
**Transfer Characteristics**



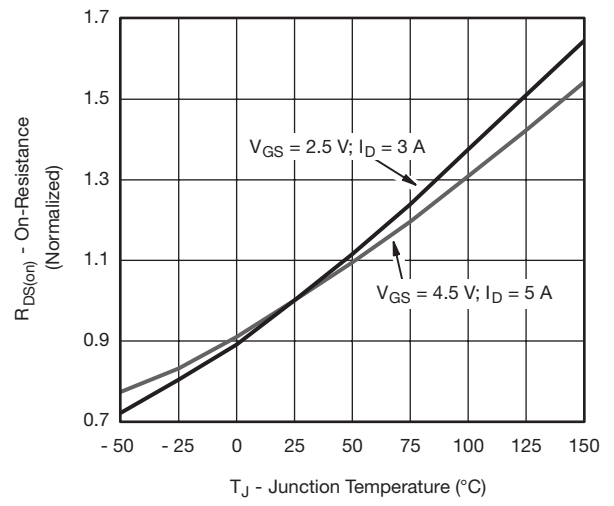
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

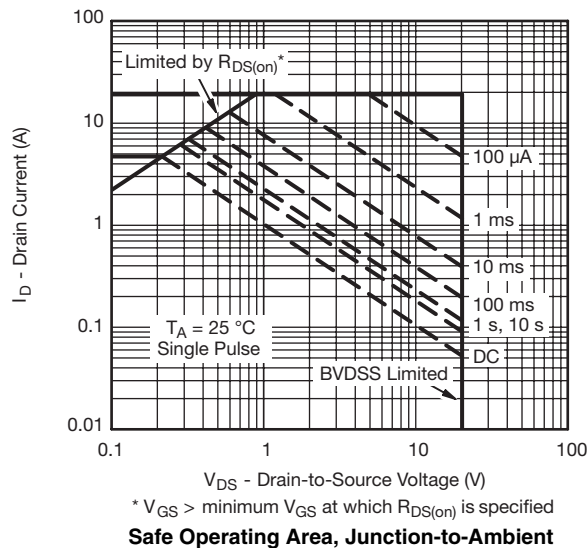
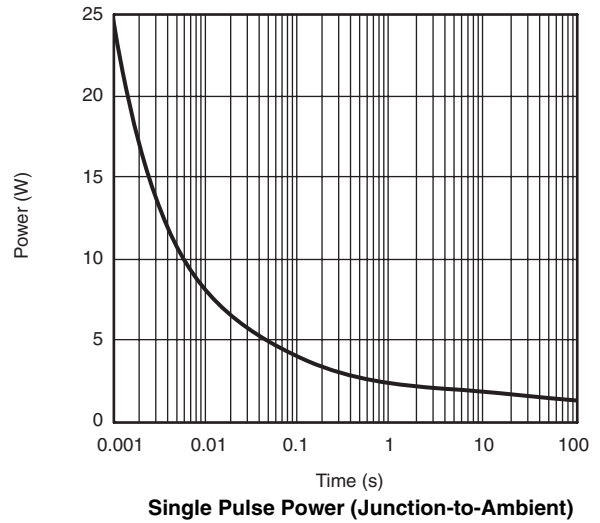
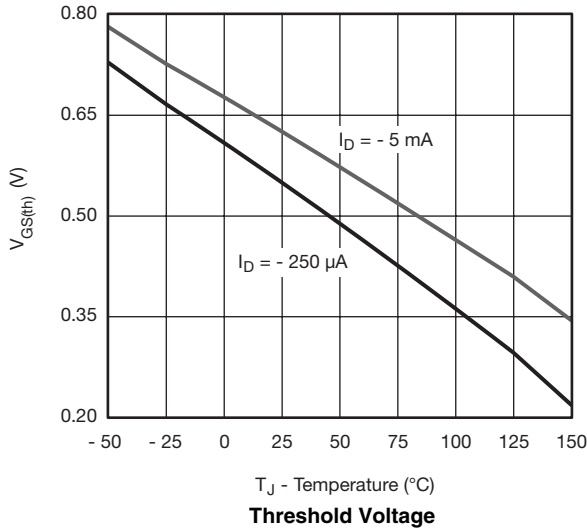
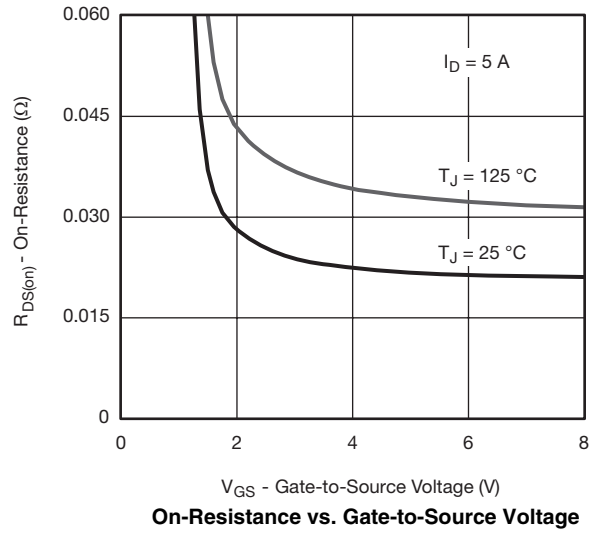
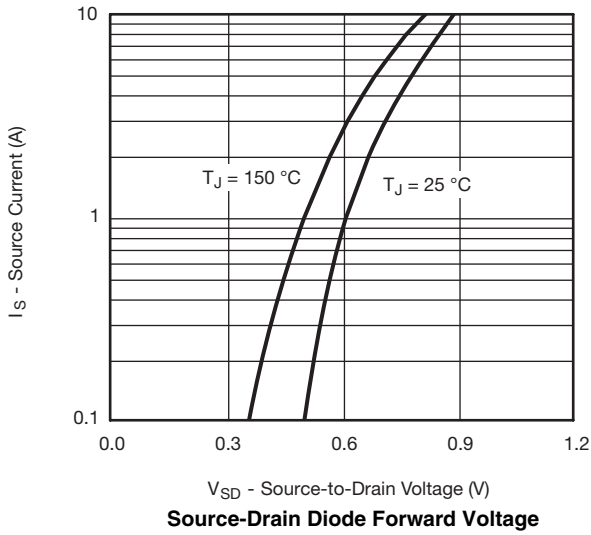


**Gate Charge**

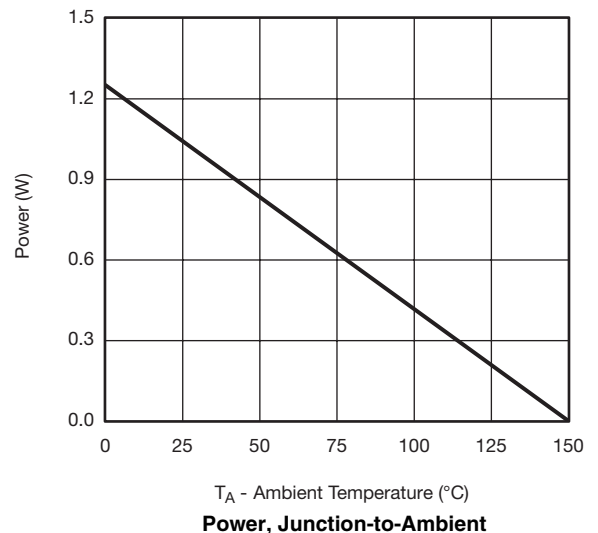
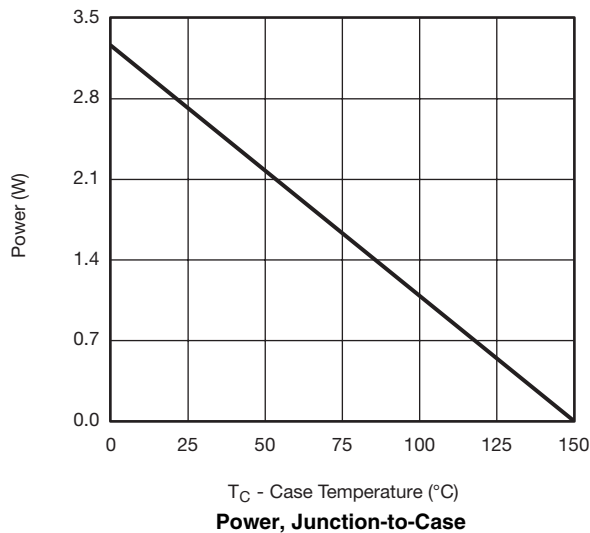
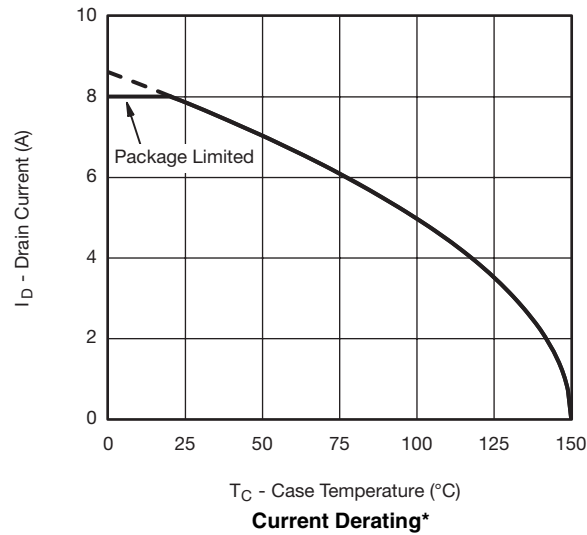


**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

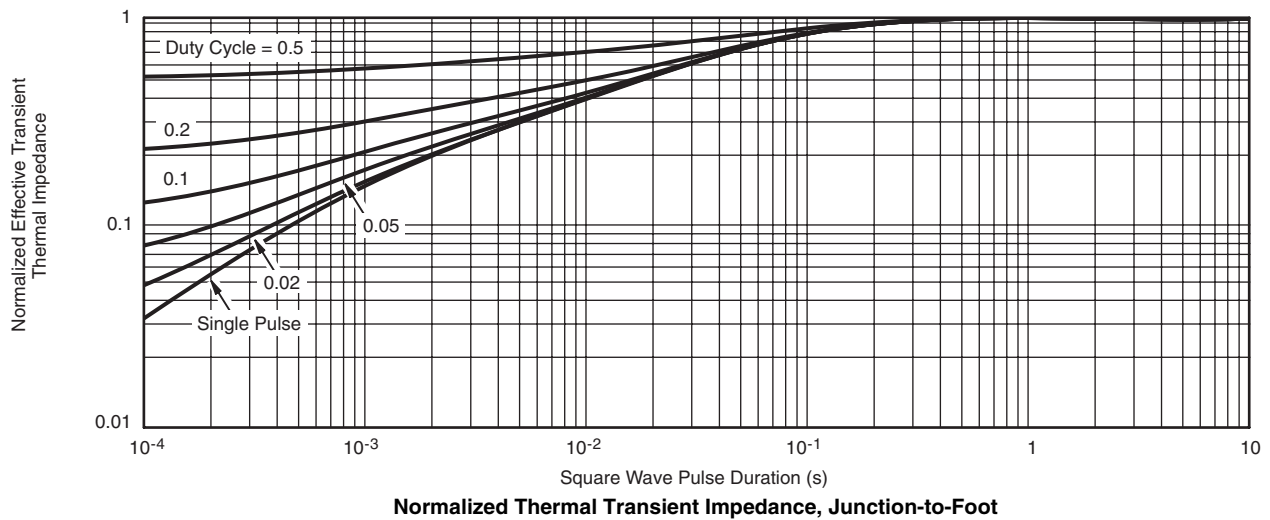
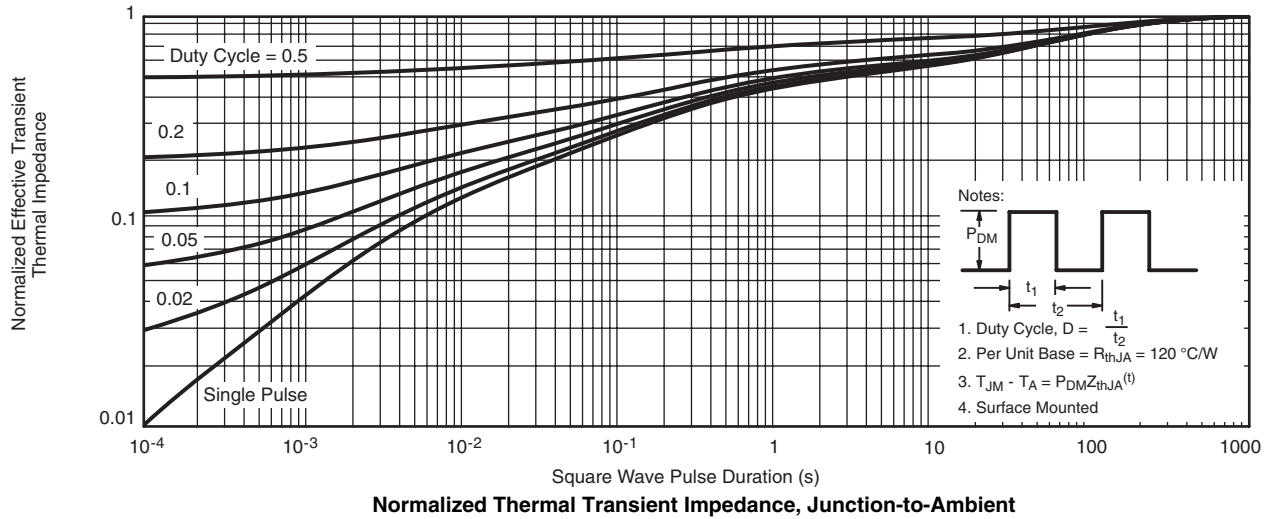


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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## TSOP: 5/6-LEAD

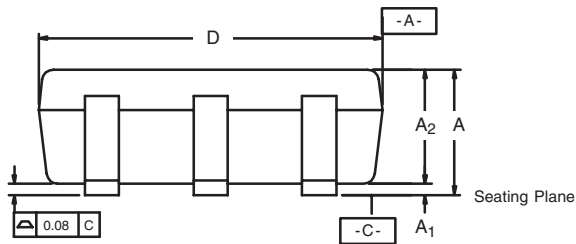
JEDEC Part Number: MO-193C



5-LEAD TSOP



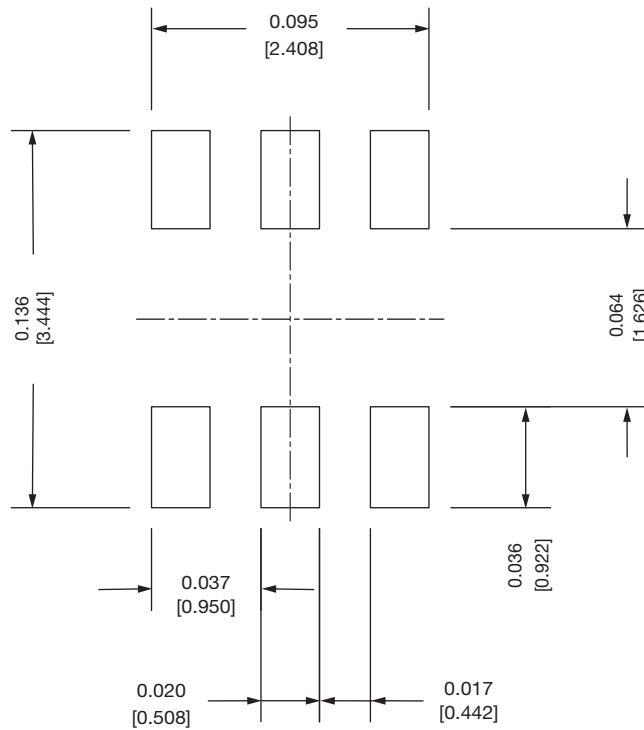
6-LEAD TSOP



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
<b>A</b>	0.91	-	1.10	0.036	-	0.043
<b>A<sub>1</sub></b>	0.01	-	0.10	0.0004	-	0.004
<b>A<sub>2</sub></b>	0.90	-	1.00	0.035	0.038	0.039
<b>b</b>	0.30	0.32	0.45	0.012	0.013	0.018
<b>c</b>	0.10	0.15	0.20	0.004	0.006	0.008
<b>D</b>	2.95	3.05	3.10	0.116	0.120	0.122
<b>E</b>	2.70	2.85	2.98	0.106	0.112	0.117
<b>E<sub>1</sub></b>	1.55	1.65	1.70	0.061	0.065	0.067
<b>e</b>	0.95 BSC			0.0374 BSC		
<b>e<sub>1</sub></b>	1.80	1.90	2.00	0.071	0.075	0.079
<b>L</b>	0.32	-	0.50	0.012	-	0.020
<b>L<sub>1</sub></b>	0.60 Ref			0.024 Ref		
<b>L<sub>2</sub></b>	0.25 BSC			0.010 BSC		
<b>R</b>	0.10	-	-	0.004	-	-
<b>θ</b>	0°	4°	8°	0°	4°	8°
<b>θ<sub>1</sub></b>	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						



# Recommended Land Pattern For TSOP-5L / TSOP-6L



**Note**

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022  
 DWG: 3010





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